

## Silicon Epitaxial Planar Transistor

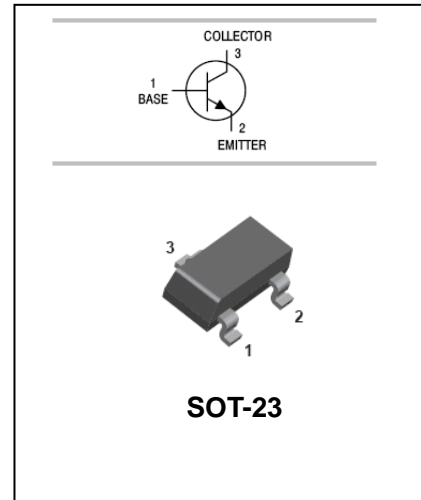
## S9014

### FEATURES

- Complementary To S9015.
- Excellent  $H_{FE}$  Linearity.
- Power dissipation. ( $P_C=0.2W$ )



Lead-free



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### APPLICATIONS

- Per-Amplifier low level & low noise.

### ORDERING INFORMATION

| Type No. | Marking | Package Code |
|----------|---------|--------------|
| S9014    | J6      | SOT-23       |

### MAXIMUM RATING @ $T_a=25^{\circ}C$ unless otherwise specified

| Symbol         | Parameter                        | Value   | Units       |
|----------------|----------------------------------|---------|-------------|
| $V_{CBO}$      | Collector-Base Voltage           | 50      | V           |
| $V_{CEO}$      | Collector-Emitter Voltage        | 45      | V           |
| $V_{EBO}$      | Emitter-Base Voltage             | 5       | V           |
| $I_C$          | Collector Current -Continuous    | 100     | mA          |
| $P_C$          | Collector Dissipation            | 200     | mW          |
| $T_j, T_{stg}$ | Junction and Storage Temperature | -55~150 | $^{\circ}C$ |

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### ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

| Parameter                            | Symbol        | Test conditions                    | MIN | TYP | MAX  | UNIT    |
|--------------------------------------|---------------|------------------------------------|-----|-----|------|---------|
| Collector-base breakdown voltage     | $V_{(BR)CBO}$ | $I_C=100\mu A, I_E=0$              | 50  |     |      | V       |
| Collector-emitter breakdown voltage  | $V_{(BR)CEO}$ | $I_C=0.1mA, I_B=0$                 | 45  |     |      | V       |
| Emitter-base breakdown voltage       | $V_{(BR)EBO}$ | $I_E=-100\mu A, I_C=0$             | 5   |     |      | V       |
| Collector cut-off current            | $I_{CBO}$     | $V_{CB}=50V, I_E=0$                |     |     | 0.1  | $\mu A$ |
| Collector cut-off current            | $I_{CEO}$     | $V_{CE}=35V, I_B=0$                |     |     | 0.1  | $\mu A$ |
| Emitter cut-off current              | $I_{EBO}$     | $V_{EB}=3V, I_C=0$                 |     |     | 0.1  | $\mu A$ |
| DC current gain                      | $h_{FE}$      | $V_{CE}=5V, I_C=1mA$               | 200 |     | 1000 |         |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | $I_C=100mA, I_B=5mA$               |     |     | 0.3  | V       |
| Base-emitter saturation voltage      | $V_{BE(sat)}$ | $I_C=100mA, I_B=5mA$               |     |     | 1    | V       |
| Transition frequency                 | $f_T$         | $V_{CE}=6V, I_C=20mA$<br>$f=30MHz$ |     | 150 |      | MHz     |

### CLASSIFICATION OF $h_{FE(1)}$

| Rank  | L       | H        |
|-------|---------|----------|
| Range | 200-450 | 450-1000 |

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TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

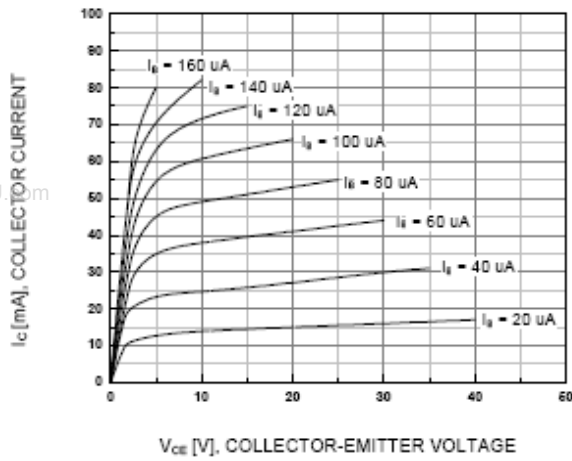


Figure 1. Static Characteristic

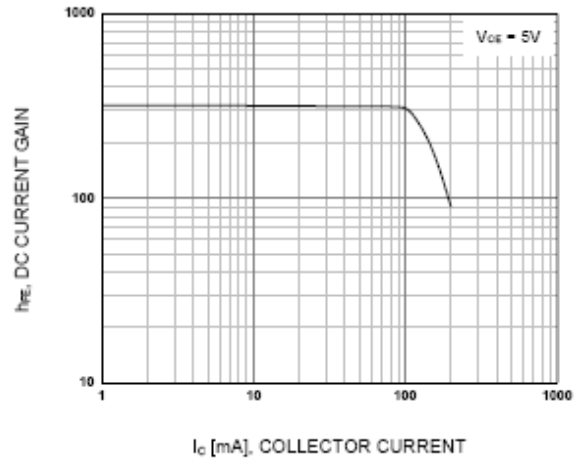


Figure 2. DC current Gain

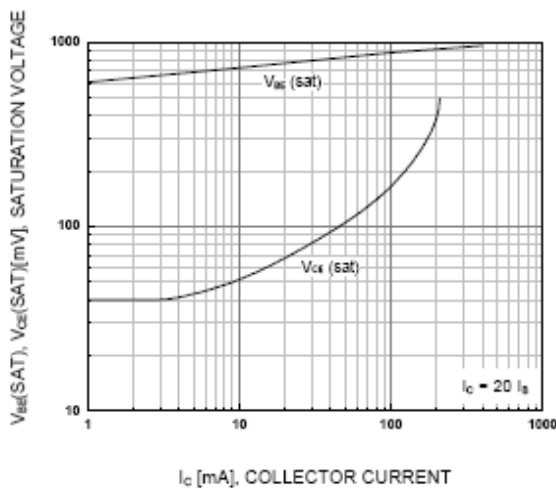


Figure 3. Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage

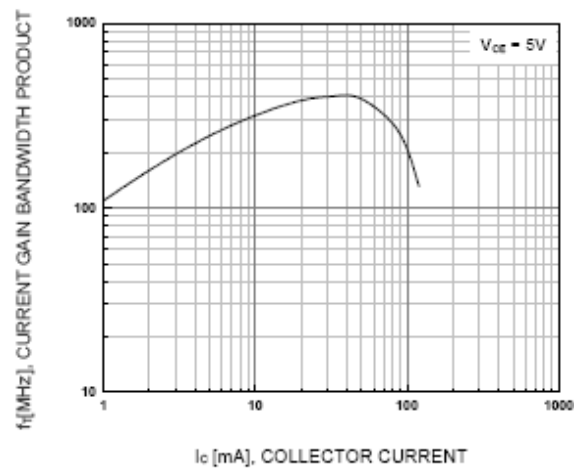


Figure 4. Current Gain Bandwidth Product

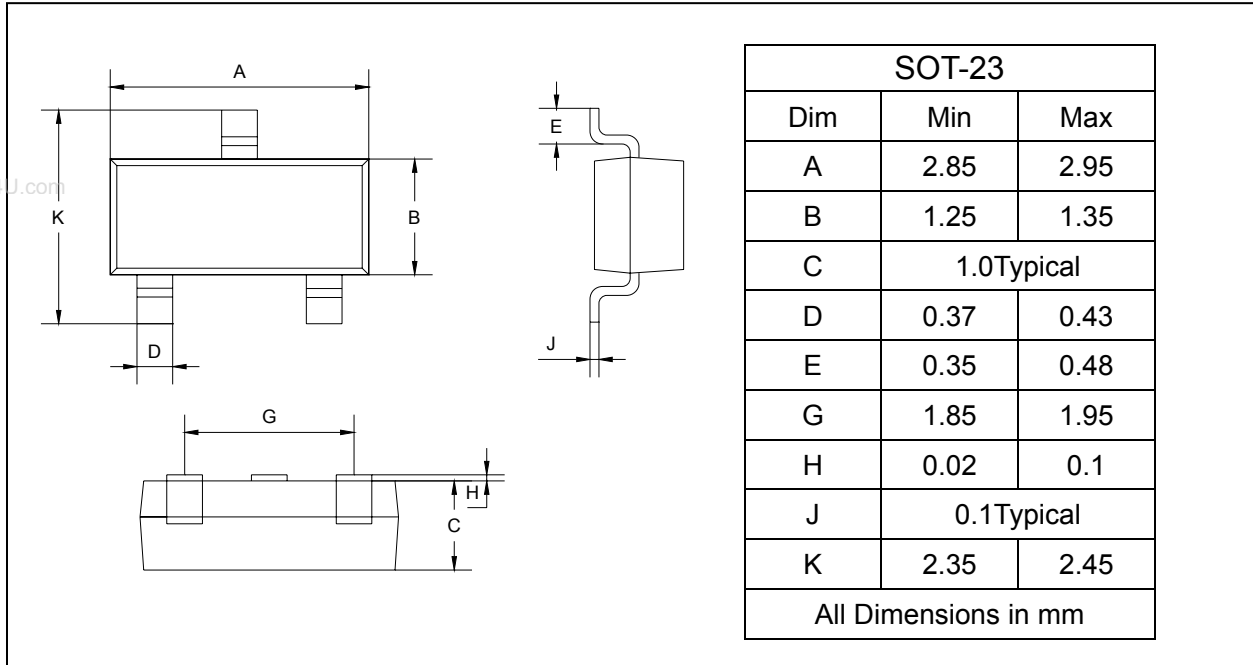
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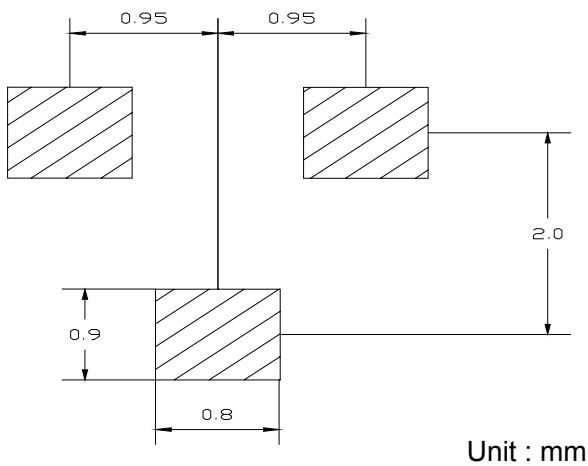
### PACKAGE OUTLINE

Plastic surface mounted package

SOT-23



### SOLDERING FOOTPRINT



### PACKAGE INFORMATION

| Device | Package | Shipping       |
|--------|---------|----------------|
| S9014  | SOT-23  | 3000/Tape&Reel |